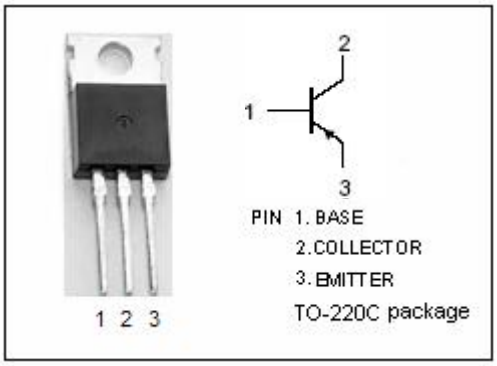
isc Silicon PNP Power Transistor — KSE45H11

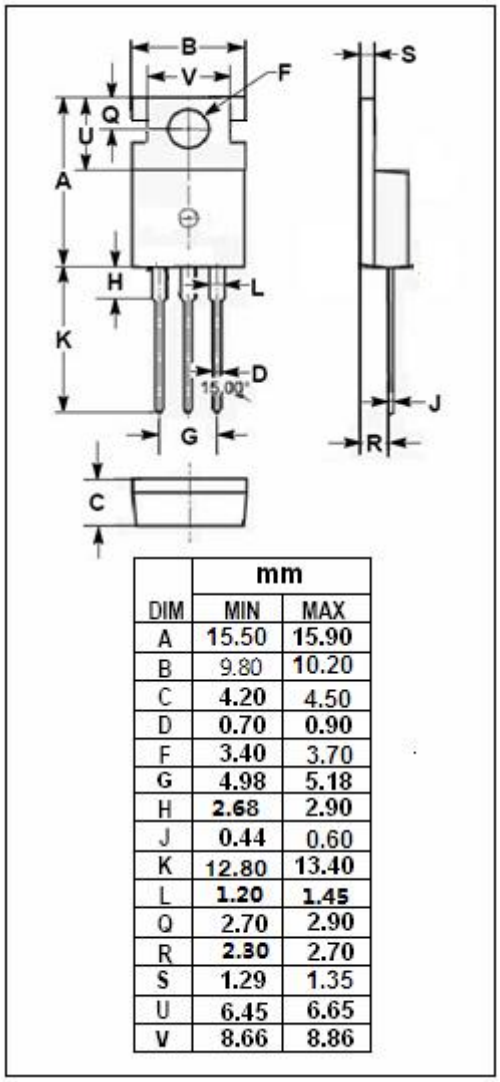


DESCRIPTION

- Collector-Emitter Breakdown Voltage
  : $V_{(BR)CEO}$= -80V(Min)
- High DC Current Gain
  : h_{FE}= 60(Min)@ (V_{CE}= -1V, I_C= -2A)
- Low Saturation Voltage-
  : $V_{CE(sat)}$= −1.0V(Max)@ (I_C= -8A, I_B= -0.4A)
- Complement to Type KSE44H11
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use as a driver in DC/DC converters and actuators.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CP}	Collector Current-Pulse	-20	A
P_C	Total Power Dissipation @ T_C=25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$*	Collector-Emitter Breakdown Voltage	I_C= -30mA; I_B= 0	-80		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -8A; I_B= -400mA		-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C=8A; I_B= 800mA		-1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -80V; I_E= 0		-10	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-50	uA
h_{FE-1}	DC Current Gain	I_C= -2A; V_{CE}= -1V	60		
h_{FE-2}	DC Current Gain	I_C= -4A; V_{CE}= -1V	40		

*:Pulse test PW≤300us,duty cycle≤2%